



WANSEMI
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WX012D06DPA

Enhancement Mode N-Channel Power MOSFET

PDFN5X6/NMOS/60V/ $\pm 20V$ /1.6V/28A/12m Ω

Rev0.1



60V, 12mΩ, 28A, Dual N-Channel MOSFET

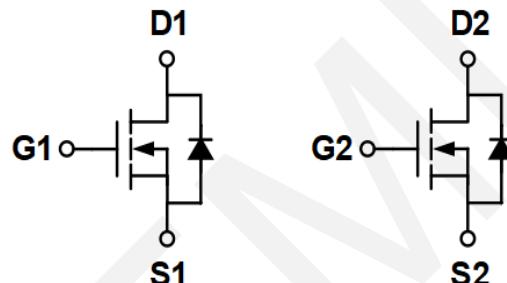
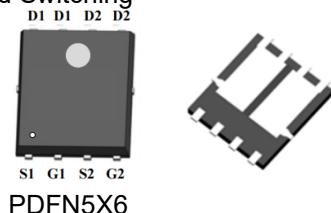
1. Features

- ◆ 60V MOSFET technology
- ◆ Low on-state resistance
- ◆ Fast switching
- ◆ $V_{GS} \pm 20V$
- ◆ 100% RG Tested
- ◆ 100% UIS Tested

V_{DS}	$R_{DS(on)}$ Typ.	I_D Max.
60V	12mΩ @ 10V	28A
	16mΩ @ 4.5V	

2. Applications

- ◆ Power Switching Application
- ◆ Load Switching



Schematic Diagram

Pin Description

3. Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WX012D06DPA	012D06D	PDFN5x6	5,000	50,000

4. Absolute Max Ratings at $T_a=25^\circ C$ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	60	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current (DC)	I_D	28	A
Drain Current (Pulse), $PW \leq 300\mu s$	I_{DP}	112	A
Total Dissipation	P_D	60	W
Avalanche Energy, Single Pulsed	E_{AS}	121	mJ
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**5.Thermal Resistance Ratings (Note 2)**

Parameter	Symbol	Value	Unit
Junction to case	R _{AJC}	2.1	°C/W

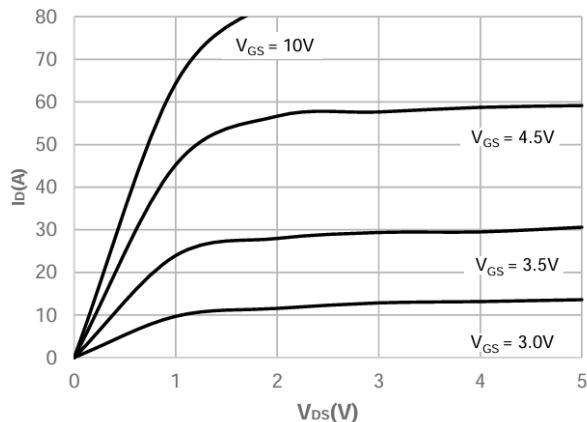
Note 2: When mounted on 1 inch square copper board $t \leq 10\text{sec}$ The value in any given application depends on the user's specific board design.

6.Electrical Characteristics at Ta=25°C (Note 3)

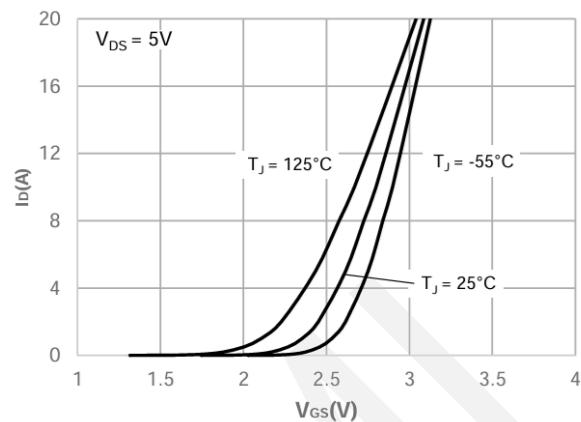
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	V _{(BR)DSS}	I _D = 250μA, V _{GS} = 0V	60	-	-	V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V	-	-	1	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.5	V
Static Drain to Source On-State Resistance	R _{DS(on)}	I _D = 15A, V _{GS} = 10V	-	12	16	mΩ
	R _{DS(on)}	I _D = 10A, V _{GS} = 4.5V	-	16	23	mΩ
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	593	-	pF
Output Capacitance	C _{oss}		-	287	-	pF
Reverse Transfer Capacitance	C _{rss}		-	18	-	pF
Turn-ON Delay Time	t _{d(on)}	V _{DD} = 30V, I _D = 20A V _{GS} = 10V, R _G = 3Ω	-	5.5	-	ns
Rise Time	t _r		-	29	-	ns
Turn-OFF Delay Time	t _{d(off)}		-	15	-	ns
Fall Time	t _f		-	3.4	-	ns
Total Gate Charge	Q _g	V _{DS} = 30V, V _{GS} = 0 to 10V, I _D = 20A	-	11	-	nC
	Q _{gs}		-	2.3	-	nC
	Q _{gd}		-	2.4	-	nC
Diode Forward Voltage	V _{FSD}	I _S = 15A, V _{GS} = 0V	-	-	1.3	V

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

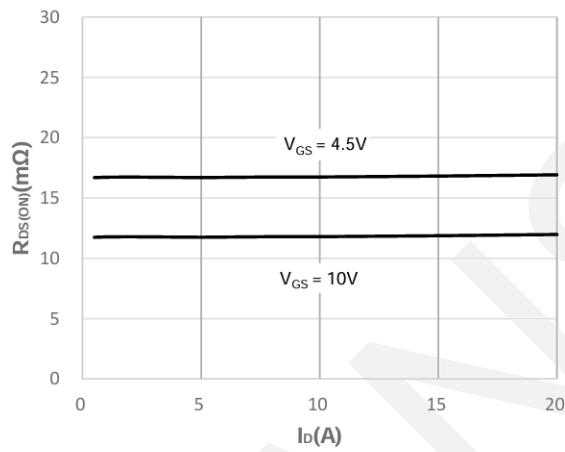
7.Typical electrical and thermal characteristics



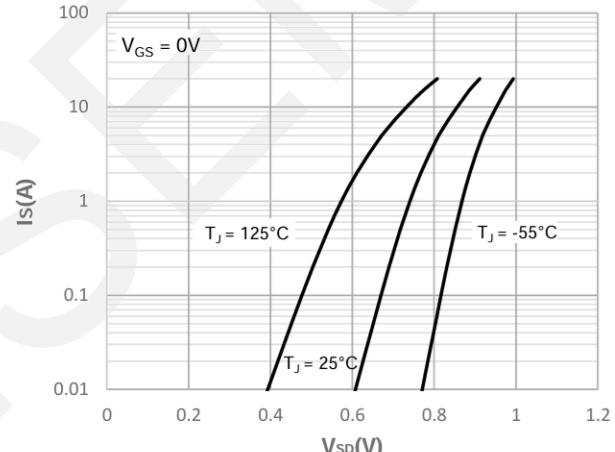
Output Characteristics



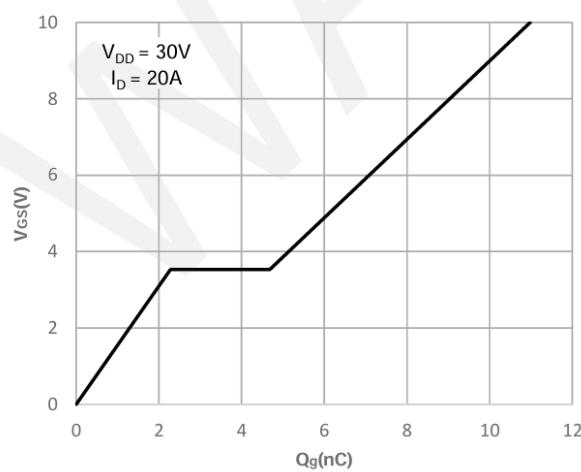
Typical Transfer Characteristics



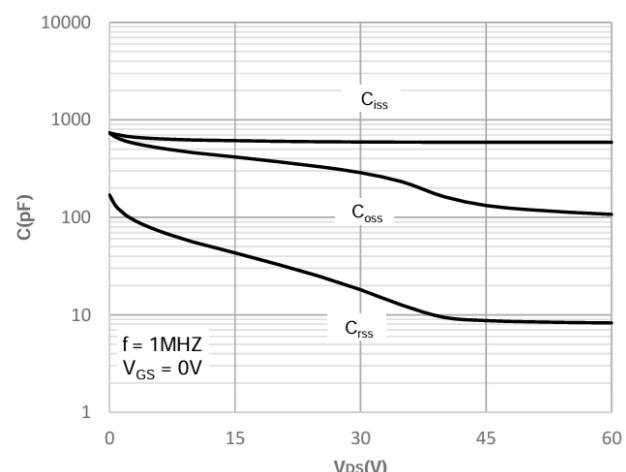
On-resistance vs. Drain Current



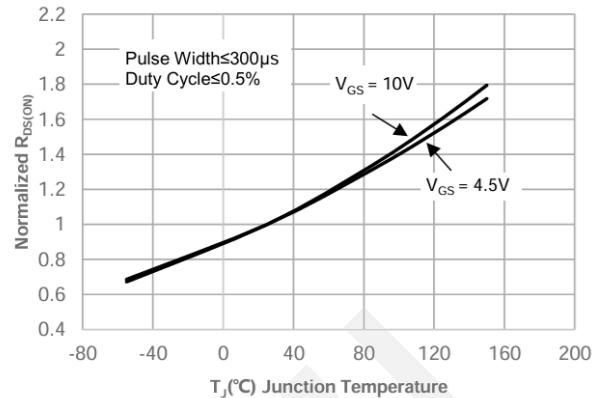
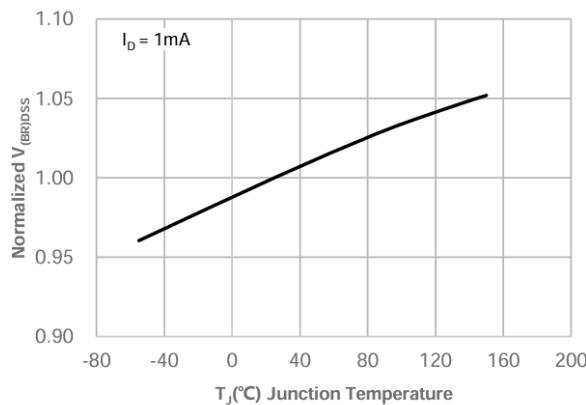
Body Diode Characteristics



Gate Charge Characteristics

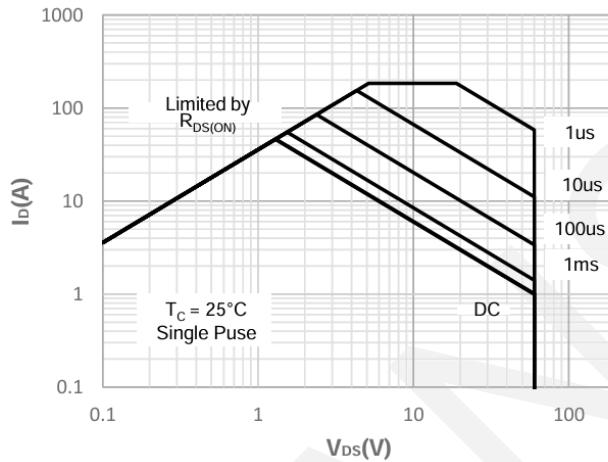


Capacitance Characteristics

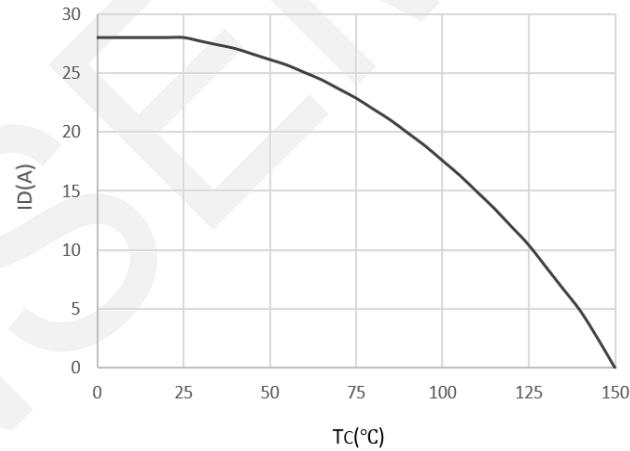


Normalized Breakdown Voltage vs.
Junction Temperature

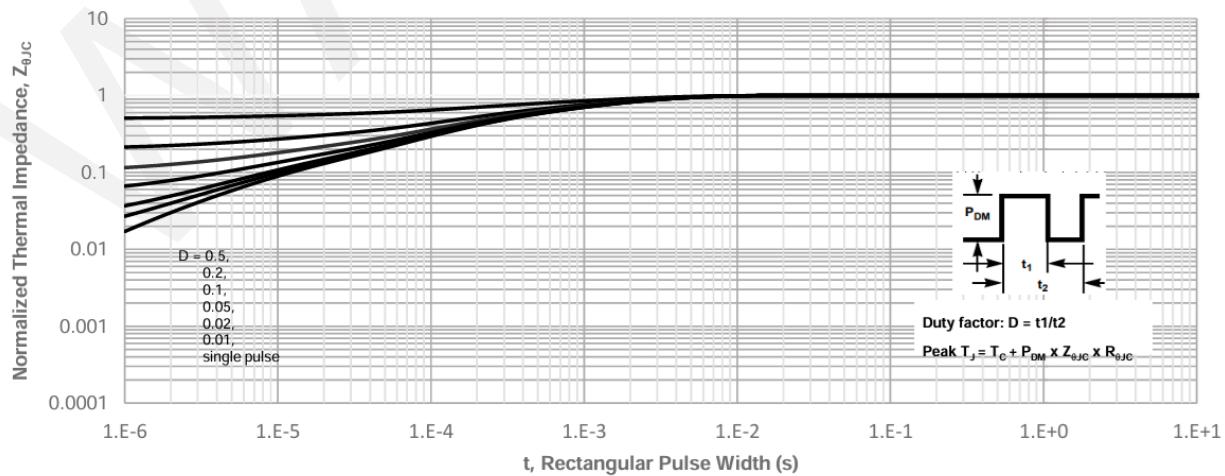
Normalized on Resistance vs.
Junction Temperature



Maximum Safe Operating Area



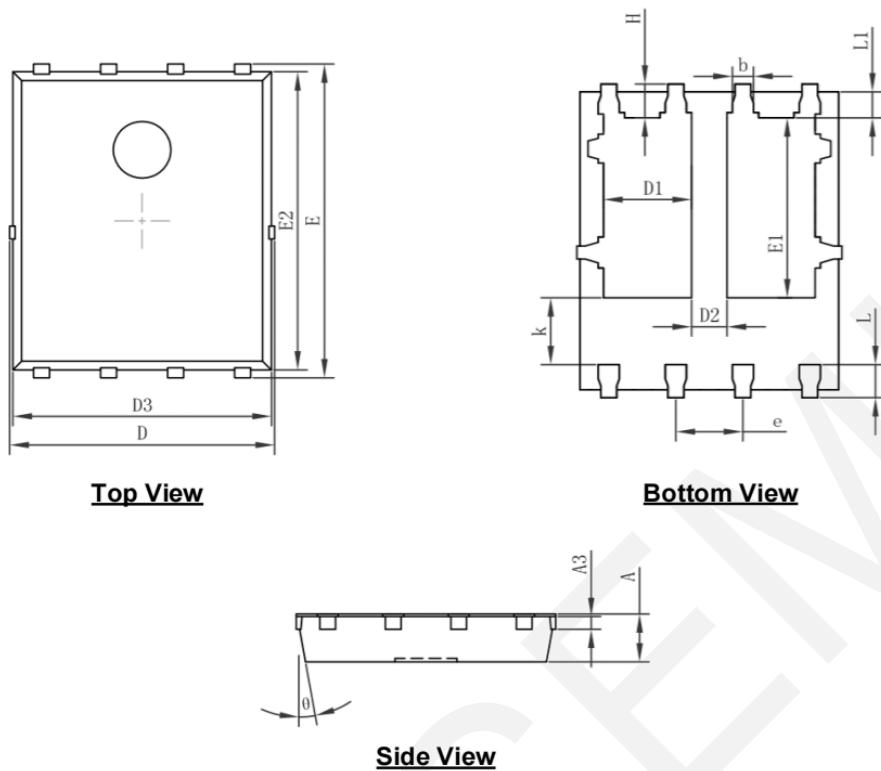
Maximum Continuous Drain Current vs.
Case Temperature



Normalized Maximum Transient Thermal Impedance



8.Package Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.154REF.		0.006REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

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